L Number	Hits	Search Text	DB	Time stamp
1	114	@ad<=20001107 and 'bottom gate TFT'	USPAT;	2002/12/18 08:50
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	1
	1.		IBM TDB	
-	36	@ad<=20001107 and 'thin film transistor'	USPAT;	2002/12/17 15:55
		and 'selective' near 'doping'	US-PGPUB;	
·			EPO; JPO;	
			DERWENT;	
	ŀ		IBM TDB	
-	2	@ad<=20001107 and 'thin film transistor'	USPAT;	2002/07/16 14:53
		and 'cleaning' near 'native oxide'	US-PGPUB;	
			EPO; JPO;	1
			DERWENT;	1
	ŀ		IBM TDB	
-	1	@ad<=20001107 and 'TFT' and 'cleaning'	USPAT;	2002/07/16 14:53
		near 'native oxide'	US-PGPUB;	
			EPO; JPO;	1
			DERWENT;	
			IBM TDB	
-	18	The state of the s	USPAT;	2002/12/17 16:10
	1	'native oxide'	US-PGPUB;	
	1		EPO; JPO;	
			DERWENT;	
1			IBM TDB	
-	7	@ad<=20001107 and 'TFT' and 'removal' near	USPAT;	2002/07/16 15:06
	i	'native oxide'	US-PGPUB;	1202,01,10 13.00
	-		EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	590	@ad<=20001107 and "thin film transistor"	USPAT;	2002/07/16 15:26
		and "ohmic contact layer"	US-PGPUB;	2002/07/10 15.20
			EPO; JPO;	
	,		DERWENT;	
			IBM TDB	
-	60	@ad<=20001107 and "thin film transistor"	USPAT;	2002/07/17 08:43
		and "remove" near 'oxide'	US-PGPUB;	2002/01/11/00:45
}			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	1	"3859716".PN.	USPAT	2002/07/16 17:05
-	1	"4757026".PN.	USPAT	2002/07/16 17:05
_	1	"4876213".PN.	USPAT	2002/07/16 17:05
-	1	"5182620".PN.	USPAT	2002/07/16 17:06
-	1	"5266823".PN.	USPAT	2002/07/16 17:06
-	1	"5323042".PN.	USPAT	2002/07/16 17:06
-	1	"5998841".PN.	USPAT	2002/07/16 17:06
-	1	"5962872".PN.	USPAT	2002/07/16 17:06
-	1	"5939731".PN.	USPAT	2002/07/16 17:07
-	1	"5804471".PN.	USPAT	2002/07/16 17:07
-	1	"5856689".PN.	USPAT	2002/07/16 17:08
-	1	"5804471".PN.	USPAT	2002/07/16 17:08
	3055	((438/149) or (438/158) or (438/315) or	USPAT;	2002/12/17 15:39
		(438/334)).CCLS.	US-PGPUB;	
1			EPO; JPO;	İ
	'		DERWENT:	
			IBM TDB	
-	6	(((438/149) or (438/158) or (438/315) or	USPAT;	2002/12/17 15:50
	1	(438/334)).CCLS.) and @ad<=20001107 and	US-PGPUB;	
]		"thin film transistor" and "remove" near	EPO; JPO;	
	ĺ	'oxide'	DERWENT;	
	ļ		IBM TDB	
[-	608	(((438/149) or (438/158) or (438/315) or	USPAT;	2002/07/17 08:46
		(438/334)).CCLS.) and @ad<=20001107 and	US-PGPUB;	2302,07,17 00.40
		"thin film transistor"	EPO; JPO;	
			DERWENT;	
			IBM TDB	i

-	5525	((438/149) or (438/158-159) or (438/315)	USPAT;	2002/12/17 15:43
	0020	or (438/334) or (438/163) or (438/166) or	US-PGPUB;	2002/12/1/ 13:43
		(257/69) or (257/72) or (257/59)).CCLS.	EPO; JPO;	i
		(2017 037 02 (2017 12) 02 (2017 3377 10083.	DERWENT;	
	İ		IBM TDB	1
_	16	(((438/149) or (438/158-159) or (438/315)	USPAT:	2002/12/17 15:51
		or (438/334) or (438/163) or (438/166) or	US-PGPUB;	2002/12/17 13:51
	1	(257/69) or (257/72) or (257/59)).CCLS.)	EPO; JPO;	
		and @ad<=20001107 and "thin film	DERWENT;	
		transistor" and "remove" near 'oxide'	IBM TDB	
_	1		USPAT;	2002/12/17 15:56
	_	and 'burried gate'	US-PGPUB;	2002/12/1/ 15:56
		and builted gate	EPO; JPO;	1
			DERWENT;	1
			IBM TDB	
_	30430	@ad<=20001107 and 'thin film transistor'	USPAT;	2002/12/17 15:59
		caa 2000110, and chin lilm clansiscol	US-PGPUB;	2002/12/1/ 15:59
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	779	(@ad<=20001107 and 'thin film transistor'	_	2002/12/17 16:01
	111) and short same channel	USPAT; US-PGPUB;	2002/12/17 16:01
		did Short Same Chamier	EPO; JPO;	
			DERWENT;	1
				1
_	719	(@ad<=20001107 and 'thin film transistor'	IBM_TDB	1 2002 (12 (17 16 20)
	,13) and short same channel and gate	USPAT;	2002/12/17 16:02
		, and short same channel and gate	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	18	@ad<=20001107 and 'TFT' and 'remove' near	IBM_TDB USPAT;	0000/10/10 00 50
	10	'native oxide'		2002/12/18 08:50
		native oxide	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	1
_	1	"5641974".PN.	IBM_TDB	2000/10/17 16 10
_	1	"5780871".PN.	USPAT	2002/12/17 16:13
_	1 1	"5837619".PN.	USPAT	2002/12/17 16:13
_	1	"5882165".PN.	USPAT	2002/12/17 16:14
_	1 1	"5917571".PN.	USPAT	2002/12/17 16:14
_	1 1	"6177302".PN.	USPAT	2002/12/17 16:14
_		((257/59) or (257/61) or (257/72) or	USPAT	2002/12/17 16:14
	4/0/	(257/347) or $(257/61)$ or $(257/72)$ or $(257/347)$ or $(349/42-43))$. CCLS.	USPAT;	2002/12/17 16:18
		(23//34/) OI (349/42-43)).CCLS.	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	1

L Number	Hits	Search Text	DB	Time stamp
1	114	@ad<=20001107 and 'bottom gate TFT'	USPAT;	2002/12/18 08:50
i			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	36	@ad<=20001107 and 'thin film transistor'	USPAT;	2002/12/17 15:55
		and 'selective' near 'doping'	US-PGPUB;	2002/12/1/ 13.33
		doping	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	2	@ad<=20001107 and 'thin film transistor'	USPAT;	2002/07/16 14:53
İ	_	and 'cleaning' near 'native oxide'	US-PGPUB;	2002/07/16 14:53
		and ordanizing near matrix oxide	EPO; JPO;	1
	1		DERWENT;	
	İ		IBM TDB	
_	1	@ad<=20001107 and 'TFT' and 'cleaning'		0000/07/16 14 50
	_	near 'native oxide'	USPAT;	2002/07/16 14:53
		Hear Hacive Oxide	US-PGPUB;	
			EPO; JPO;	
	1		DERWENT;	
1_	18	0 d < - 20001107 1 Impm: 1	IBM_TDB	1
-	1.0	data legal did legal did legal	USPAT;	2002/12/17 16:10
	1	'native oxide'	US-PGPUB;	
			EPO; JPO;	
	1.		DERWENT;	1
	_		IBM_TDB	
-	7	@ad<=20001107 and 'TFT' and 'removal' near	USPAT;	2002/07/16 15:06
		'native oxide'	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	590	@ad<=20001107 and "thin film transistor"	USPAT;	2002/07/16 15:26
		and "ohmic contact layer"	US-PGPUB;	2002/07/10 13:20
		•	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	60	@ad<=20001107 and "thin film transistor"	USPAT;	2002/07/17 08:43
		and "remove" near 'oxide'	US-PGPUB;	2002/07/17 00:45
			EPO; JPO;	1
			DERWENT;	
	-		IBM TDB	
_	1	"3859716".PN.	USPAT	2002/07/16 17 05
1- 1		"4757026".PN.	USPAT	2002/07/16 17:05
_		"4876213".PN.		2002/07/16 17:05
-	ī	"5182620".PN.	USPAT	2002/07/16 17:05
_ [1	"5266823".PN.	USPAT	2002/07/16 17:06
	1	"5323042".PN.	USPAT	2002/07/16 17:06
_	. 1	"5998841".PN.	USPAT	2002/07/16 17:06
_	1	"5962872".PN.	USPAT	2002/07/16 17:06
[<u> </u>			USPAT	2002/07/16 17:06
1_	1	"5939731".PN.	USPAT	2002/07/16 17:07
-	1	"5804471". PN.	USPAT	2002/07/16 17:07
-	1	"5856689".PN.	USPAT	2002/07/16 17:08
-	1	"5804471".PN.	USPAT	2002/07/16 17:08
-	3055	((438/149) or (438/158) or (438/315) or	USPAT;	2002/12/17 15:39
		(438/334)).CCLS.	US-PGPUB;	
			EPO; JPO;	
		I	DERWENT;	
			IBM TDB	
-	6	(((438/149) or (438/158) or (438/315) or	USPAT;	2002/12/17 15:50
[(438/334)).CCLS.) and @ad<=20001107 and	US-PGPUB;	12, 22, 23, 30
1	İ	"thin film transistor" and "remove" near	EPO; JPO;	1
		'oxide'	DERWENT;	
			IBM TDB	
-	608	(((438/149) or (438/158) or (438/315) or	USPAT;	2002/07/17 08:46
		(438/334)).CCLS.) and @ad<=20001107 and	US-PGPUB;	2002/01/11 00:40
		"thin film transistor"	EPO; JPO;	I
		Laim ClassoffCOI	DERWENT;	1
			IBM_TDB	

	5525	1 (((((((((((((((((((1110000	10000/10/17 15
] -	5525	1 (1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	USPAT;	2002/12/17 15:43
		or (438/334) or (438/163) or (438/166) or	US-PGPUB;	
		(257/69) or (257/72) or (257/59)).CCLS.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	16	(((438/149) or (438/158-159) or (438/315)	USPAT;	2002/12/17 15:51
		or (438/334) or (438/163) or (438/166) or	US-PGPUB;	
		(257/69) or (257/72) or (257/59)).CCLS.)	EPO; JPO;	
		and @ad<=20001107 and "thin film	DERWENT;	
		transistor" and "remove" near 'oxide'	IBM TDB	
i -	1		USPAT;	2002/12/17 15:56
		and 'burried gate'	US-PGPUB;	2002/12/1/ 13.30
	-	l service de la constant de la const	EPO; JPO;	
			DERWENT;	
			IBM TDB	1
_	30430	@ad<=20001107 and 'thin film transistor'	USPAT;	2002/12/17 15 50
	30.50	cad 20001107 and chim film clansistor		2002/12/17 15:59
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	779	/A-200001107 111 111	IBM_TDB	
-	119	(@ad<=20001107 and 'thin film transistor'	USPAT;	2002/12/17 16:01
) and short same channel	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	719	(@ad<=20001107 and 'thin film transistor'	USPAT;	2002/12/17 16:02
) and short same channel and gate	US-PGPUB;	
			EPO; JPO;	1
			DERWENT;	
			IBM TDB	
_	18	@ad<=20001107 and 'TFT' and 'remove' near	USPAT;	2002/12/18 08:50
	1	'native oxide'	US-PGPUB:	
			EPO; JPO;	
			DERWENT:	
	-		IBM TDB	
-	1	"5641974".PN.	USPĀT	2002/12/17 16:13
	1	"5780871".PN.	USPAT	2002/12/17 16:13
_	$\overline{1}$	"5837619".PN.	USPAT	2002/12/17 16:13
_	1 1	"5882165".PN.	USPAT	
_	î	"5917571".PN.	USPAT	2002/12/17 16:14
_	1 1	"6177302".PN.		2002/12/17 16:14
_	4767	((257/59) or (257/61) or (257/72) or	USPAT	2002/12/17 16:14
	1 3,01		USPAT;	2002/12/17 16:18
		(257/347) or (349/42-43)).CCLS.	US-PGPUB;	1
			EPO; JPO;	
			DERWENT;	
			IBM TDB	